

### Abstract of the Disclosure

The present invention relates to a method for fabricating a ferroelectric memory device. The method includes the steps of: forming a first insulation layer on a substrate; forming a storage node contact contacting to a partial portion of the substrate by passing through the first insulation layer; forming a stack pattern of a lower electrode contacting to the storage node contact and a hard mask on the first insulation layer; forming a second insulation layer on an entire surface of the resulting structure including the stack pattern; planarizing the second insulation layer until a surface of the hard mask is exposed; removing selectively the exposed hard mask to make a surface level of the lower electrode lower than that of the second insulation layer; and forming sequentially a ferroelectric layer and an upper electrode on the second insulation layer and the lower electrode.

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